Ref #	Hits	Search Query	DBs	Default Operat or	Plural	Time Stamp
L5	3	"6452271"	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/14 06:52
L6	4	"6445069"	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/14 06:55
L7	6	"6444489"	US-PGPU B; USPAT; EPO; JPO	OR	ON ,	2005/09/14 07:00
L8	1	"6424090"	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/14 07:01
L9	17	"6153940"	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/14 07:04
L10	17	"6153940"	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/14 07:05
LII	39	"3986255"	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/14
L12	16458	((bonding bond) near3 pad) with (substrate dielectric insulat\$3)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/14 07:09
L13	6774	12 and ((bonding bond) near3 pad) with (trench hole via groove aperture opening)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/14
L14	343	13 and ((mask\$3 photoresist resist) near3 pad) with (trench hole via groove aperture opening)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/14 07:11

L15	124	14 and ('cu' copper) with (trench hole via groove aperture opening)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/14 07:12
S1 :	1	:	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/13 17:33
S3	3	"6362090"	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/13
S4	17839	((dielectric insulat\$3) with (trench via hole damascene groove aperture)) with mask\$3	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/13 18:44
S5	9987	S4 and (dielectric insulat\$3) with (photoresist resist)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/13
S6	201	S5 and (dielectric insulat\$3) with (bond\$3 adj pad)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/13 18:46
S7	107	S6 and ('cu' copper interconnect\$3) with (bond\$3 adj pad)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/14 06:51